

N-Channel 30 V (D-S) MOSFET

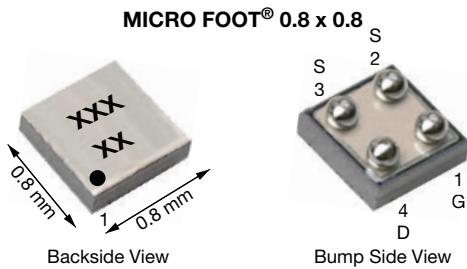
PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A) ^a	Q _g (TYP.)
30	0.095 at V _{GS} = 4.5 V	2.5	3.7 nC
	0.105 at V _{GS} = 2.5 V	2.3	
	0.120 at V _{GS} = 1.8 V	2.2	
	0.165 at V _{GS} = 1.5 V	1.9	

FEATURES

- TrenchFET® power MOSFET
- Small 0.8 mm x 0.8 mm outline area
- Low 0.4 mm max. profile
- 30 V max. rating and low on-resistance
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE



Marking Code: xx = Al

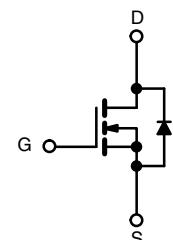
xxx = Date/Lot traceability code

Ordering Information:

Si8808DB-T2-E1 (lead (Pb)-free and halogen-free)

APPLICATIONS

- Load switch
- High speed switching
- DC/DC converters
- For smart phones, tablet PCs, and mobile computing



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	± 8	
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	2.5 ^a	A
	T _A = 70 °C	2 ^a	
	T _A = 25 °C	1.8 ^b	
	T _A = 70 °C	1.4 ^b	
Pulsed Drain Current (t = 300 μs)	I _{DM}	10	
Continuous Source-Drain Diode Current	T _A = 25 °C	0.7 ^a	
	T _A = 25 °C	0.4 ^b	
Maximum Power Dissipation	T _A = 25 °C	0.9 ^a	W
	T _A = 70 °C	0.6 ^a	
	T _A = 25 °C	0.5 ^b	
	T _A = 70 °C	0.3 ^b	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Soldering Recommendations (Peak Temperature) ^c		260	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient ^{a,d}	t ≤ 5 s	R _{thJA}	105	135
Maximum Junction-to-Ambient ^{b,e}			200	260

Notes

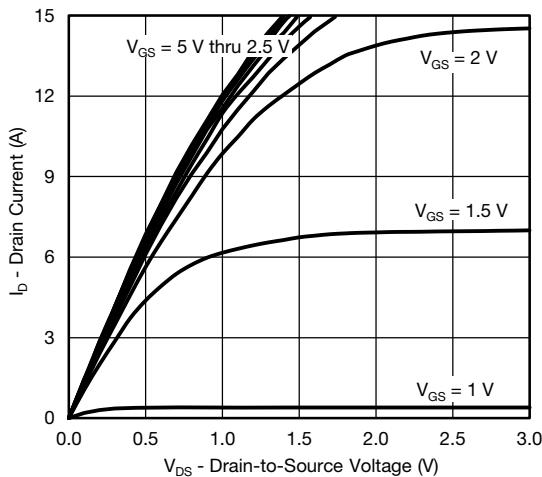
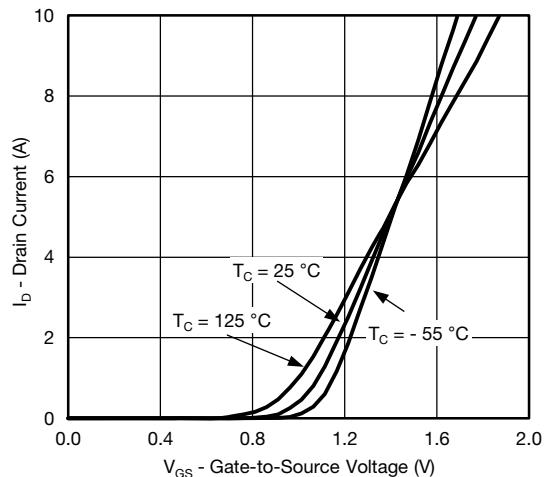
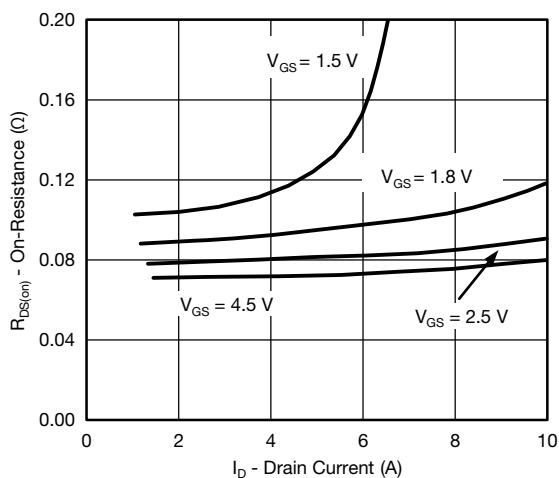
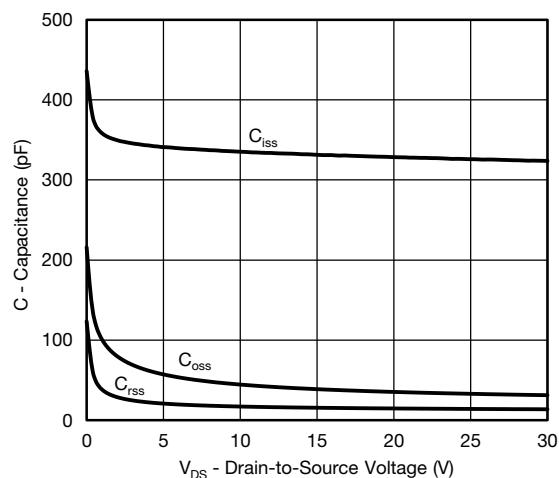
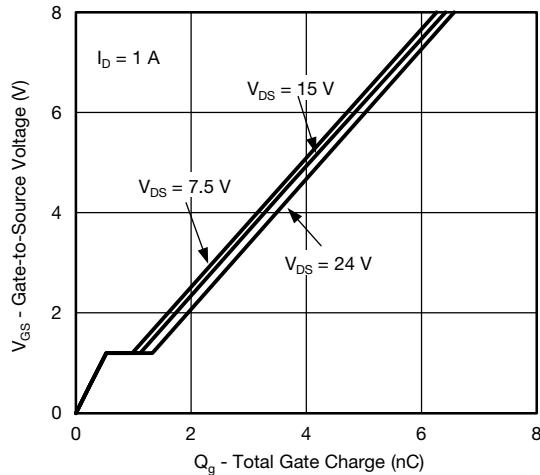
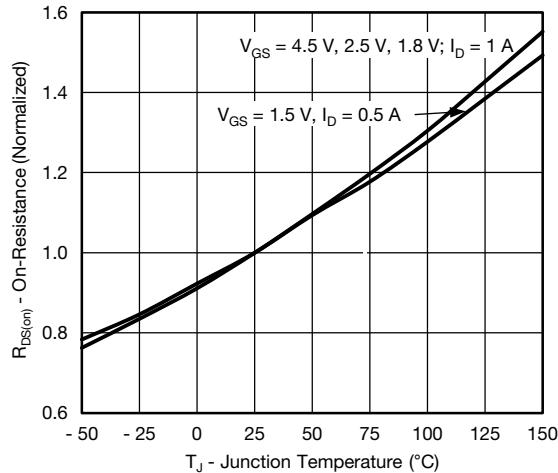
- Surface mounted on 1" x 1" FR4 board with full copper, t = 5 s.
- Surface mounted on 1" x 1" FR4 board with minimum copper, t = 5 s.
- Refer to IPC/JEDEC® (J-STD-020), no manual or hand soldering.
- Maximum under steady state conditions is 185 °C/W.
- Maximum under steady state conditions is 330 °C/W.

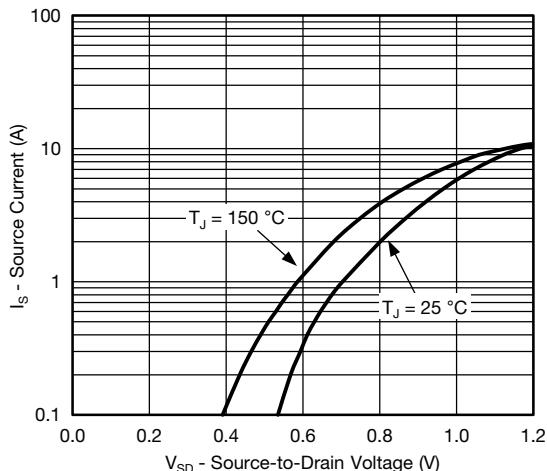
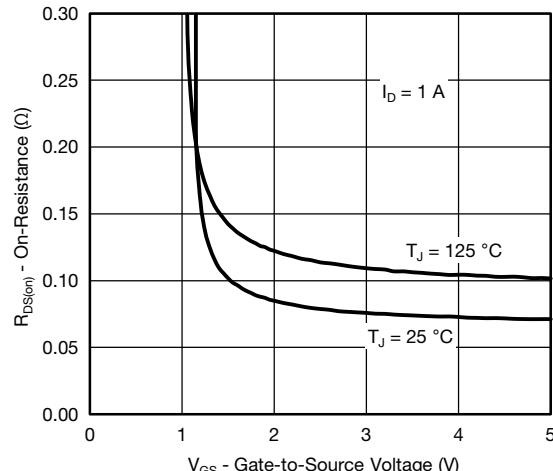
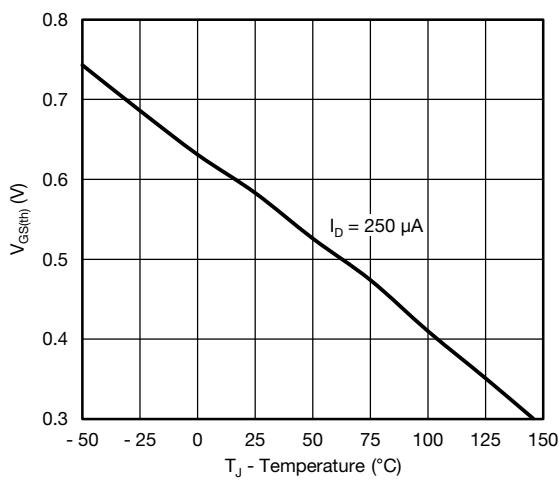
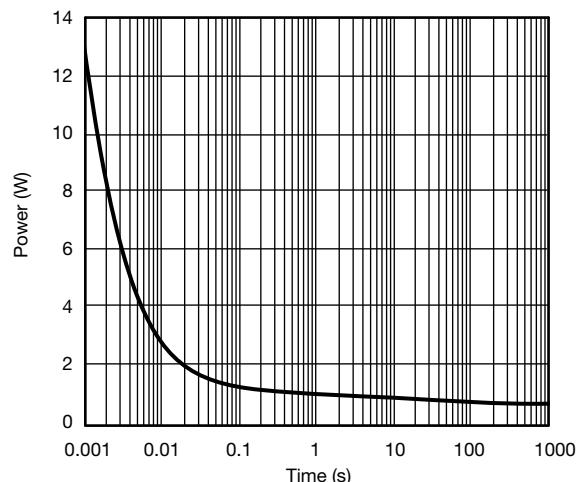
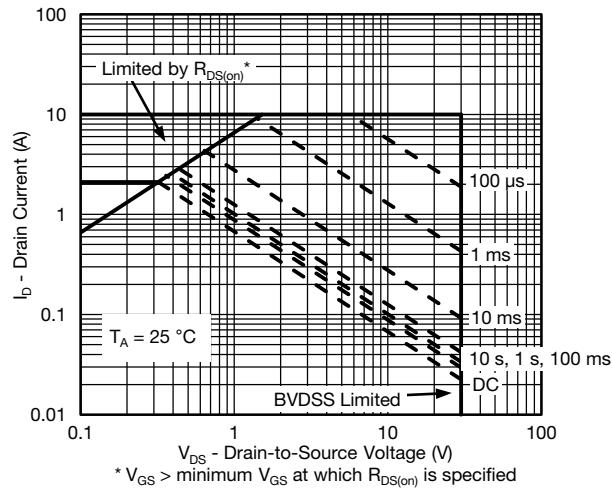
SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	30	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \mu\text{A}$	-	31	-	mV/°C
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$		-	-2.3	-	
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	0.4	-	0.9	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 8 \text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$	-	-	1	μA
		$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 55^\circ\text{C}$	-	-	10	
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}$, $V_{GS} = 4.5 \text{ V}$	5	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 4.5 \text{ V}$, $I_D = 1 \text{ A}$	-	0.071	0.095	Ω
		$V_{GS} = 2.5 \text{ V}$, $I_D = 1 \text{ A}$	-	0.079	0.105	
		$V_{GS} = 1.8 \text{ V}$, $I_D = 1 \text{ A}$	-	0.090	0.120	
		$V_{GS} = 1.5 \text{ V}$, $I_D = 0.5 \text{ A}$	-	0.105	0.165	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}$, $I_D = 1 \text{ A}$	-	10	-	S
Dynamic ^b						
Input Capacitance	C_{iss}	$V_{DS} = 15 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	-	330	-	pF
Output Capacitance	C_{oss}		-	40	-	
Reverse Transfer Capacitance	C_{rss}		-	16	-	
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}$, $V_{GS} = 8 \text{ V}$, $I_D = 1 \text{ A}$	-	6.5	10	nC
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}$, $V_{GS} = 4.5 \text{ V}$, $I_D = 1 \text{ A}$	-	3.7	5.6	
Gate-Drain Charge	Q_{gd}		-	0.53	-	
Gate Resistance	R_g		-	0.52	-	
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 15 \text{ V}$, $R_L = 15 \Omega$ $I_D \approx 1 \text{ A}$, $V_{GEN} = 8 \text{ V}$, $R_g = 1 \Omega$	-	3.1	-	Ω
Rise Time	t_r		-	5	10	ns
Turn-Off Delay Time	$t_{d(\text{off})}$		-	12	25	
Fall Time	t_f		-	15	30	
Turn-On Delay Time	$t_{d(\text{on})}$		-	6	15	
Rise Time	t_r		-	7	15	
Turn-Off Delay Time	$t_{d(\text{off})}$		-	15	30	
Fall Time	t_f		-	22	40	
-	-		-	10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_A = 25^\circ\text{C}$	-	-	0.7	A
Pulse Diode Forward Current	I_{SM}		-	-	10	
Body Diode Voltage	V_{SD}	$I_S = 1 \text{ A}$, $V_{GS} = 0 \text{ V}$	-	0.7	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 1 \text{ A}$, $dI/dt = 100 \text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$	-	11	20	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	5	10	
Reverse Recovery Fall Time	t_a		-	7	-	
Reverse Recovery Rise Time	t_b		-	4	-	

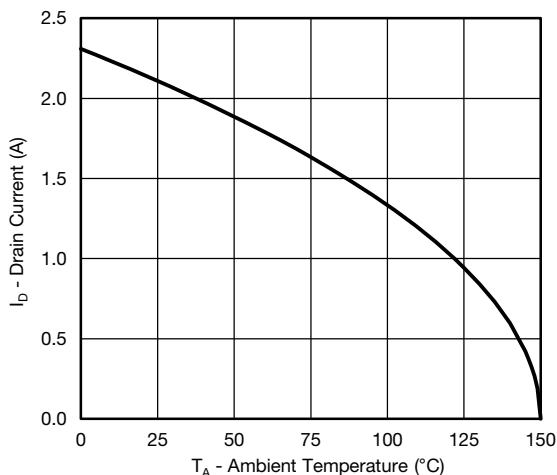
Notes

a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

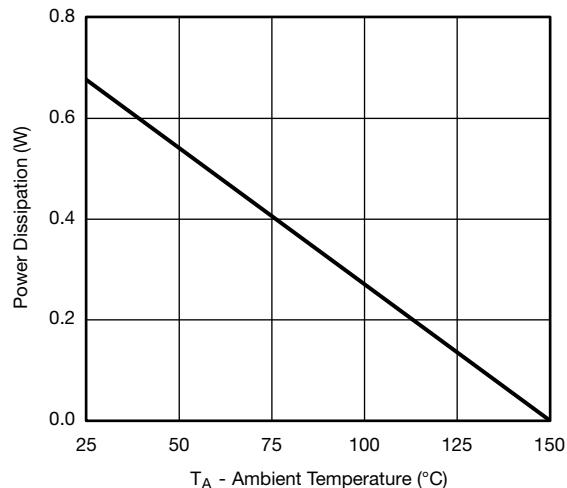
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

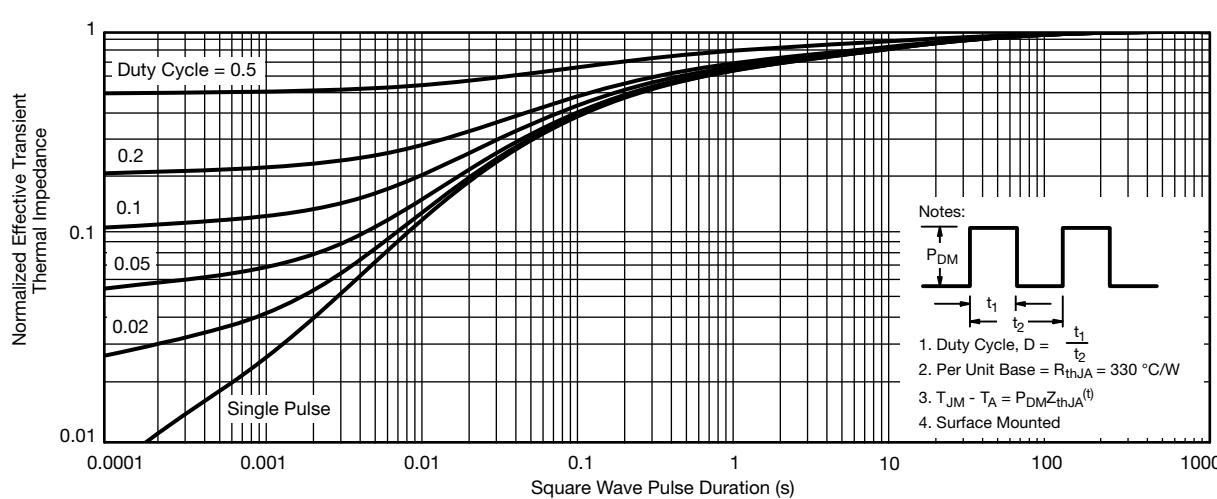
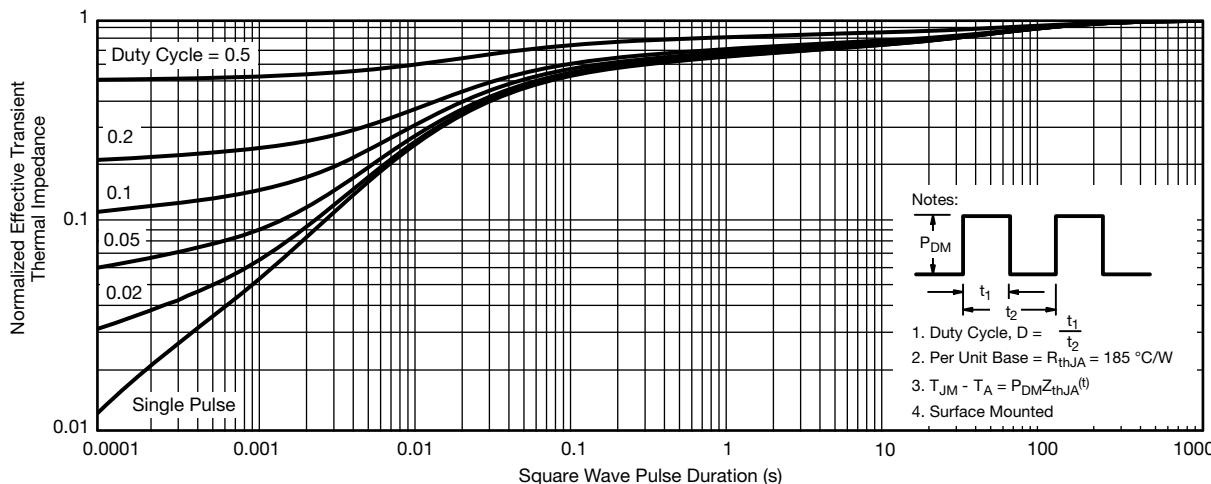
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power (Junction-to-Ambient)

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating*
Note

When mounted on 1" x 1" FR4 with full copper.

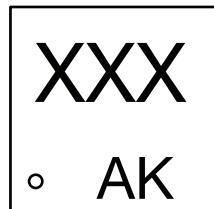

Power Derating

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

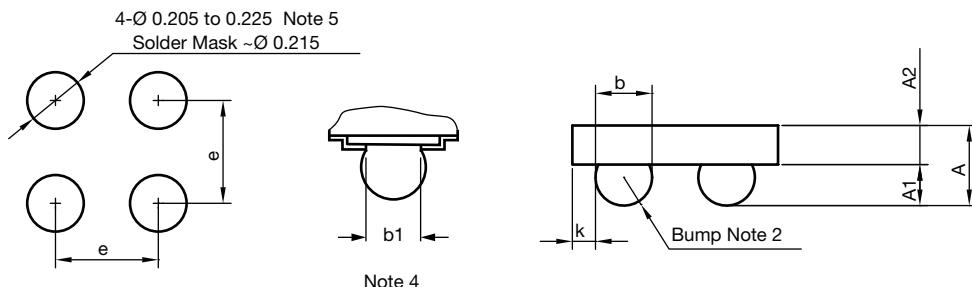
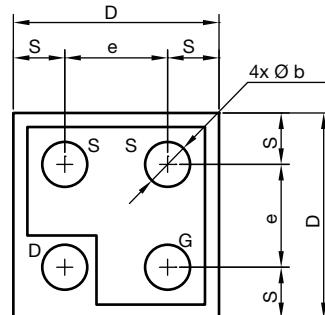
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


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MICRO FOOT®: 4-Bump (0.8 mm x 0.8 mm, 0.4 mm Pitch)



Mark on Backside of die



Notes

- (1) Laser mark on the backside surface of die
- (2) Bumps are 95.5 % Sn, 3.8 % Ag, 0.7 % Cu
- (3) "i" is the location of pin 1
- (4) "b1" is the diameter of the solderable substrate surface, defined by an opening in the solder resist layer solder mask defined.
- (5) Non-solder mask defined copper landing pad.

DIM.	MILLIMETERS ^a			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.328	0.365	0.402	0.0129	0.0144	0.0158
A1	0.136	0.160	0.184	0.0053	0.0062	0.0072
A2	0.192	0.205	0.218	0.0076	0.0081	0.0086
b	0.200	0.220	0.240	0.0078	0.0086	0.0094
b1	0.175			0.0068		
e	0.400			0.0157		
S	0.160	0.180	0.200	0.0062	0.0070	0.0078
D	0.720	0.760	0.800	0.0283	0.0299	0.0314
K	0.040	0.070	0.100	0.0015	0.0027	0.0039

Note

a. Use millimeters as the primary measurement.

ECN: T15-0053-Rev. A, 16-Feb-15

DWG: 6033

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